

## Dual N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (nC) TYP.
30	0.32 at V <sub>GS</sub> = 10 V	0.9	1.2
	0.39 at V <sub>GS</sub> = 4.5 V		

### FEATURES

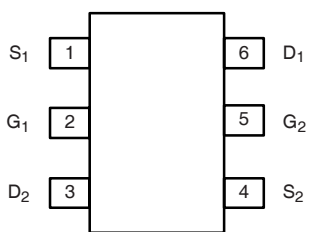
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> tested
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



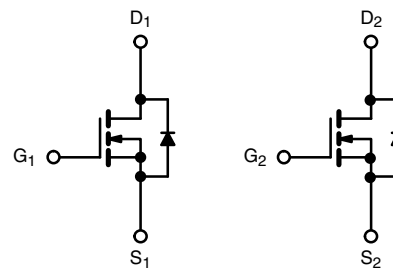
### APPLICATIONS

- Level Shifts
- Buck Converters
- Motor drives
- Low power load switch

SOT-323-6



Top View



N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	0.9
		T <sub>C</sub> = 70 °C	0.72
		T <sub>A</sub> = 25 °C	0.39 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.30 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	2.5	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	0.35 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	0.32
		T <sub>C</sub> = 70 °C	0.205
		T <sub>A</sub> = 25 °C	0.25 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.16 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	450	600	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	252	400	

#### Notes

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 400 °C/W.

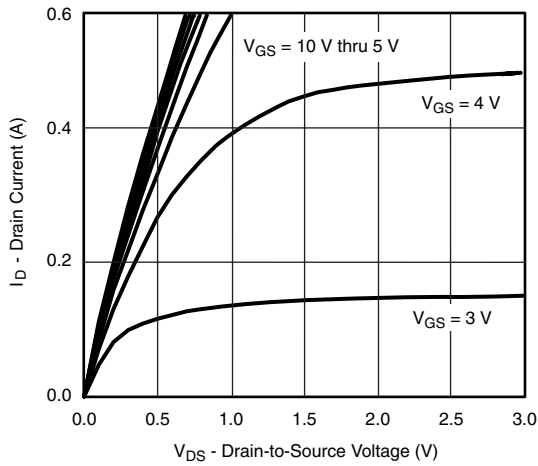
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		56.7		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.8		2	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	0.9			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.2\text{ A}$		0.32	0.82	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$		0.39	1.3	
Forward Transconductance	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 0.2\text{ A}$		105		ms
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		28		pF
Output Capacitance	$C_{oss}$			16		
Reverse Transfer Capacitance	$C_{rss}$			7		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.2\text{ A}$		1.2		nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$		0.5		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$		0.9		
Gate-Drain Charge	$Q_{gd}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$		0.4		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		160		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 100\text{ }\Omega,$ $I_D \cong 0.2\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		16		ns
Rise Time	$t_r$			32		
Turn-Off Delay Time	$t_{d(off)}$			83		
Fall Time	$t_f$			74		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Sorce-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			0.9	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				2.5	
Body Diode Voltage	$V_{SD}$	$I_S = 0.2\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 0.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		26		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			23		nC
Reverse Recovery Fall Time	$t_a$			13.5		ns
Reverse Recovery Rise Time	$t_b$			3		

**Notes**

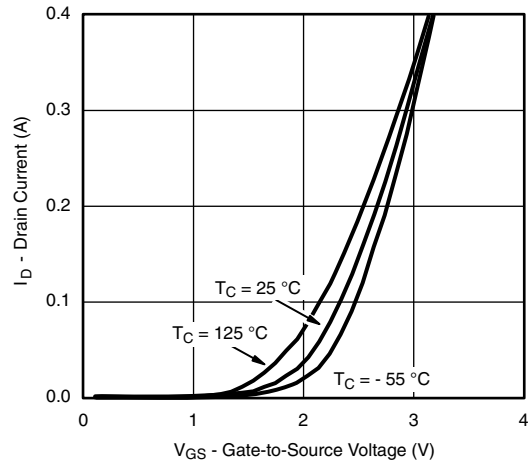
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

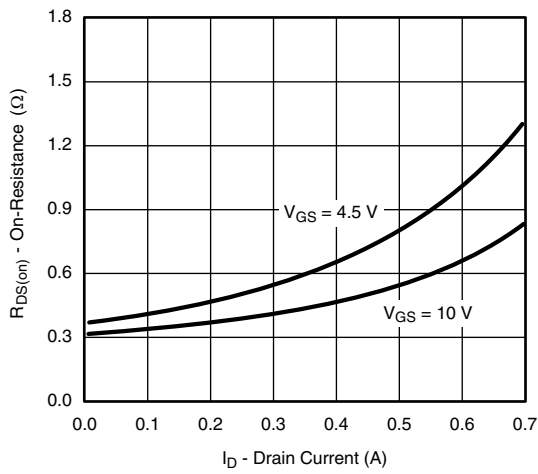
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



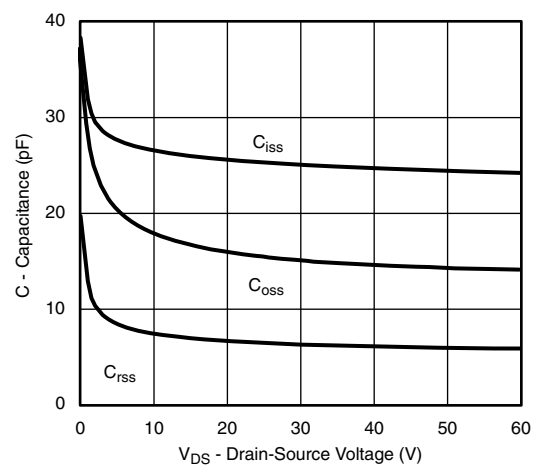
**Output Characteristics**



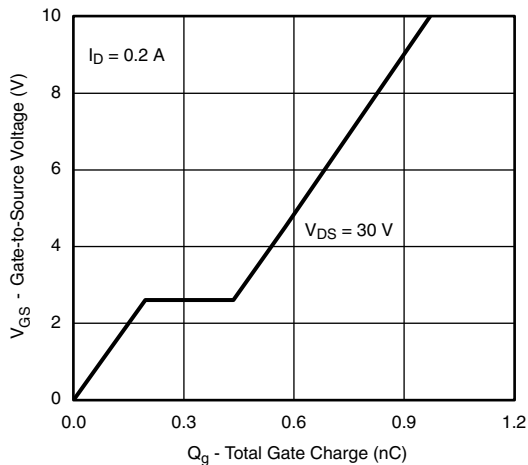
**Transfer Characteristics Curves vs. Temperature**



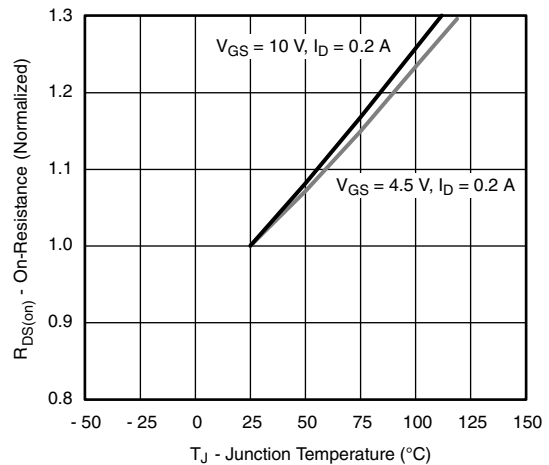
**On-Resistance vs. Drain Current**



**Capacitance**

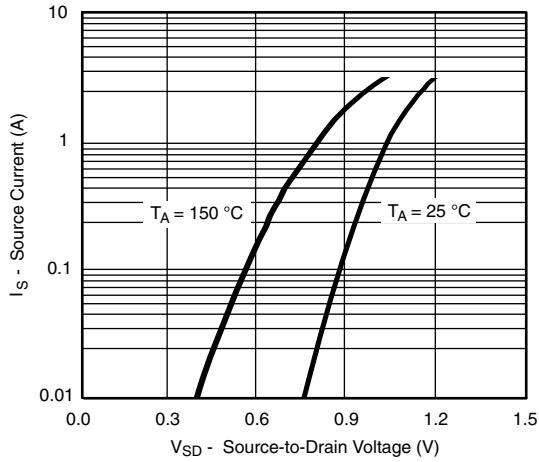


**Gate Charge**

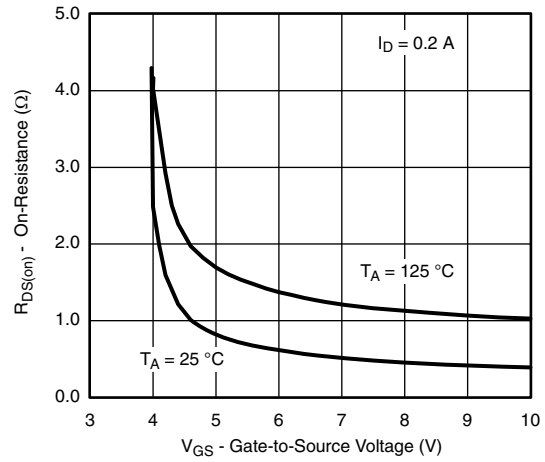


**On-Resistance vs. Junction Temperature**

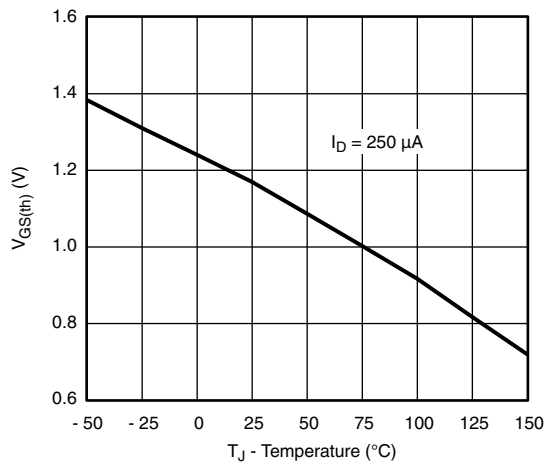
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



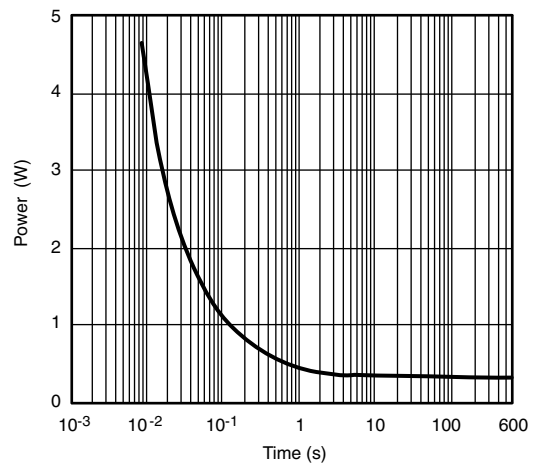
**Source-Drain Diode Forward Voltage**



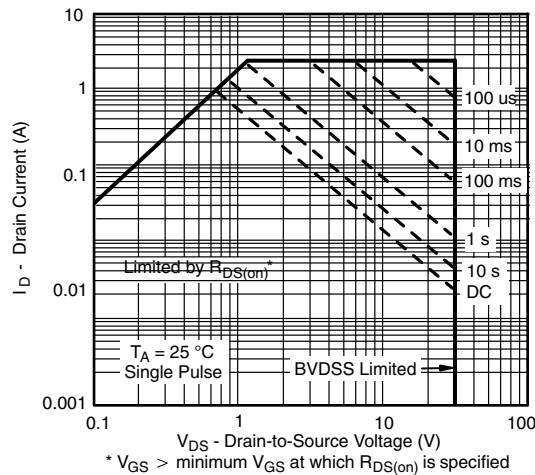
**$R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature**



**Threshold Voltage**

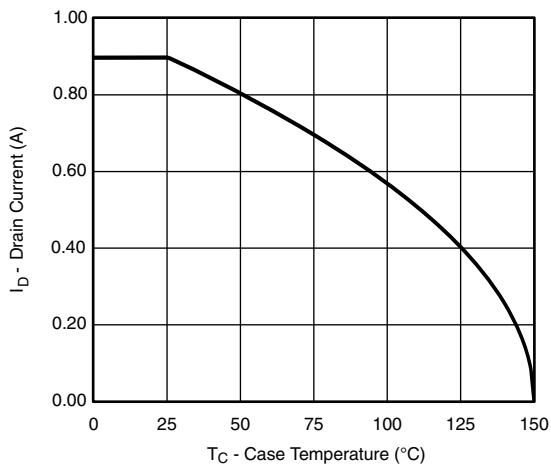


**Single Pulse Power**

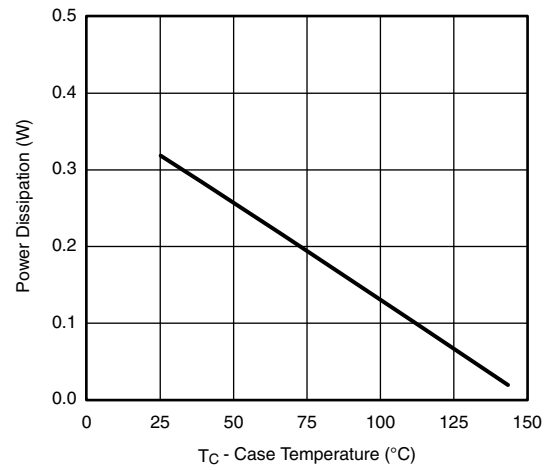


**Safe Operating Area**

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Current Derating <sup>a</sup>**

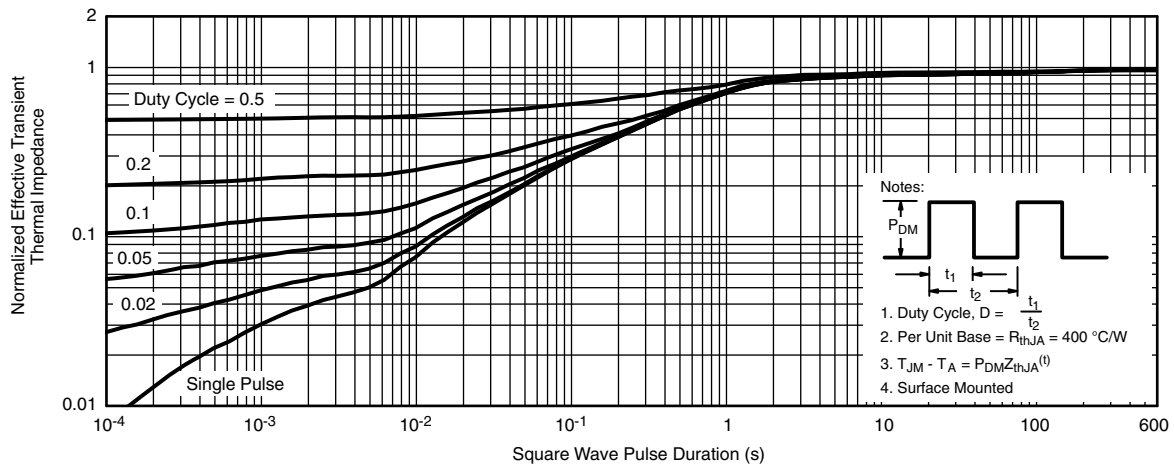


**Power Derating**

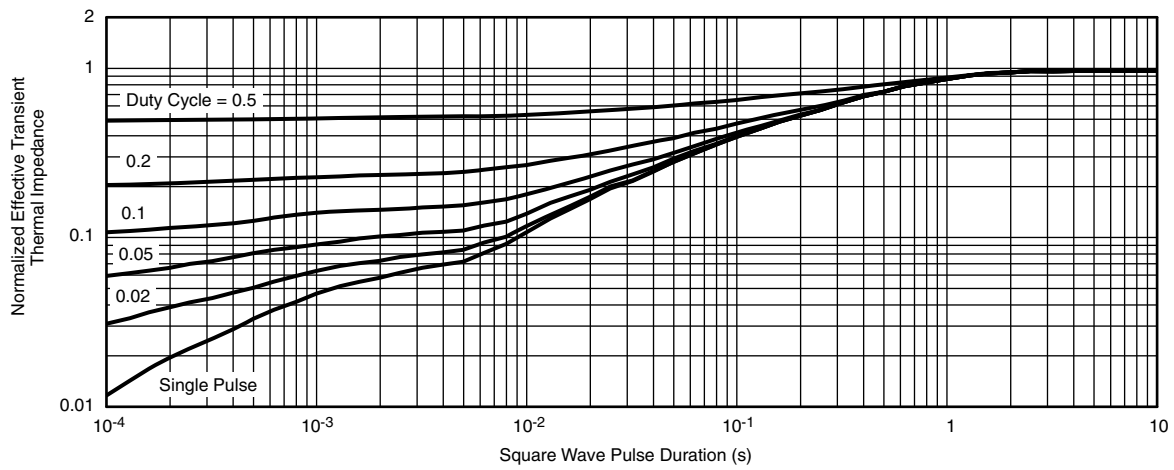
**Note**

- a. The power dissipation  $P_D$  is based on  $T_{J(\text{max.})} = 150\text{ }^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

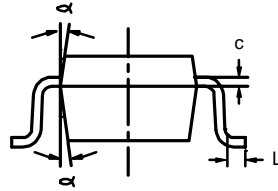
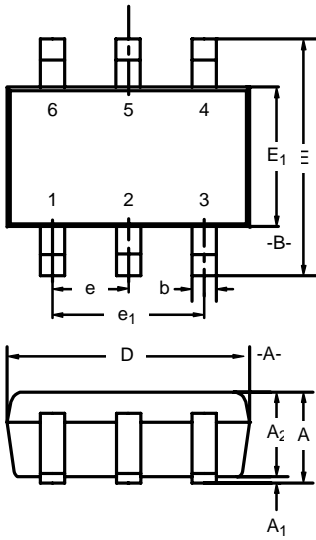
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

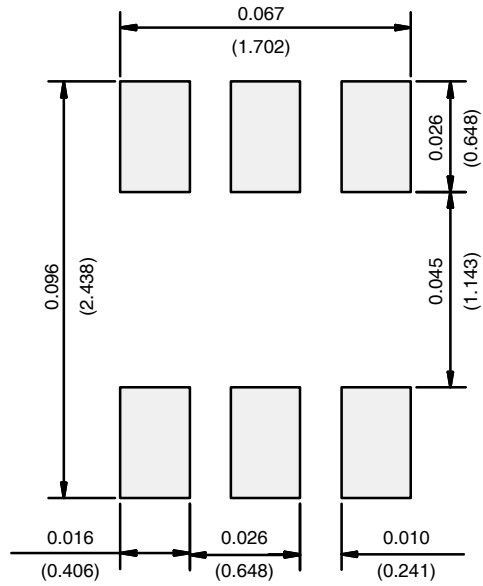


**Normalized Thermal Transient Impedance, Junction-to-Foot**



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
<b>A</b>	0.90	-	1.10	0.035	-	0.043
<b>A<sub>1</sub></b>	-	-	0.10	-	-	0.004
<b>A<sub>2</sub></b>	0.80	-	1.00	0.031	-	0.039
<b>b</b>	0.15	-	0.30	0.006	-	0.012
<b>c</b>	0.10	-	0.25	0.004	-	0.010
<b>D</b>	1.80	2.00	2.20	0.071	0.079	0.087
<b>E</b>	1.80	2.10	2.40	0.071	0.083	0.094
<b>E<sub>1</sub></b>	1.15	1.25	1.35	0.045	0.049	0.053
<b>e</b>	0.65BSC			0.026BSC		
<b>e<sub>1</sub></b>	1.20	1.30	1.40	0.047	0.051	0.055
<b>L</b>	0.10	0.20	0.30	0.004	0.008	0.012
<b>α</b>	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						

**RECOMMENDED MINIMUM PADS FOR SOT323: 6-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)



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